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FDMS2672

N-Channel UltraFET Trench MOSFET

200V, 20A, 77mΩ

Features

- Max $r_{DS(on)}$ = 77mΩ at $V_{GS} = 10V$, $I_D = 3.7A$
- Max $r_{DS(on)}$ = 88mΩ at $V_{GS} = 6V$, $I_D = 3.5A$
- Low Miller Charge
- RoHS Compliant

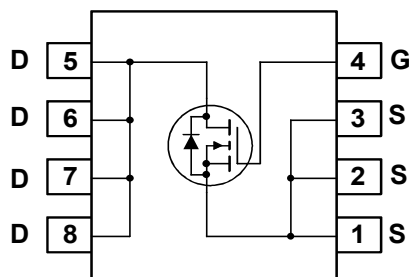
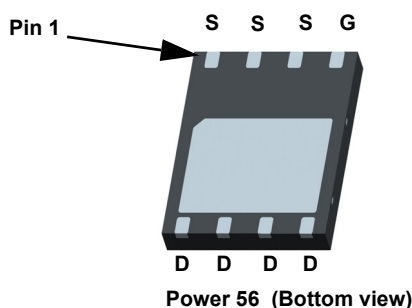


General Description

UltraFET devices combine characteristics that enable benchmark efficiency in power conversion applications. Optimized for $r_{DS(on)}$, low ESR, low total and Miller gate charge, these devices are ideal for high frequency DC to DC converters.

Application

- DC - DC Conversion



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	200	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous $T_C = 25^\circ\text{C}$ (Note 5)	20	A
	-Continuous $T_C = 100^\circ\text{C}$ (Note 5)	13	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	3.7	
	-Pulsed (Note 4)	96	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	33.8	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	78	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.6	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS2672	FDMS2672	Power 56	7"	12mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	200			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		210		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 160\text{V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2	3.1	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		-10		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 3.7\text{A}$		64	77	m Ω
		$V_{GS} = 6\text{V}$, $I_D = 3.5\text{A}$		69	88	
		$V_{GS} = 10\text{V}$, $I_D = 3.7\text{A}$, $T_J = 125^\circ\text{C}$		129	156	
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{V}$, $I_D = 3.7\text{A}$		14		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		1740	2315	pF
C_{oss}	Output Capacitance			95	125	pF
C_{rss}	Reverse Transfer Capacitance			30	45	pF
R_g	Gate Resistance		0.1	1	5	Ω

Switching Characteristics

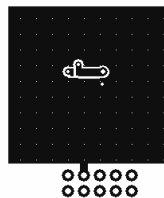
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{V}$, $I_D = 3.7\text{A}$ $V_{GS} = 10\text{V}$, $R_{GEN} = 6\Omega$		22	34	ns
t_r	Rise Time			11	22	ns
$t_{d(off)}$	Turn-Off Delay Time			36	57	ns
t_f	Fall Time			10	20	ns
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0\text{V}$ to 10V	$V_{DD} = 100\text{V}$	30	42	nC
Q_{gs}	Gate to Source Gate Charge	$I_D = 3.7\text{A}$		7		nC
Q_{gd}	Gate to Drain "Miller" Charge			8		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 3.7\text{A}$ (Note 2)		0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 3.7\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$		70	105	ns
Q_{rr}	Reverse Recovery Charge			238	357	nC

Notes:

1: $R_{\theta JA}$ is determined with the device mounted on a 1in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $50^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b. $125^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3: E_{AS} of 33.8mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 3\text{mH}$, $I_{AS} = 4.75\text{A}$, $V_{DD} = 25\text{V}$, $V_{GS} = 10\text{V}$.

4: Pulsed I_D please refer to Fig 11 SOA graph for more details.

5: Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

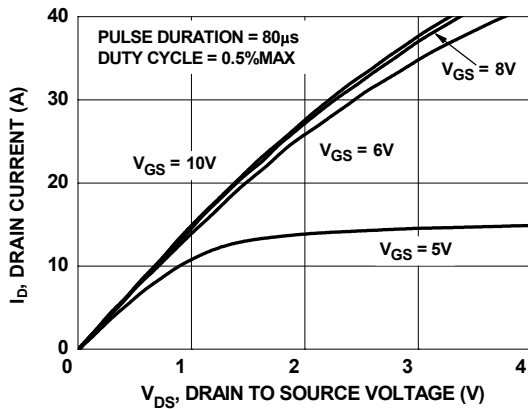


Figure 1. On Region Characteristics

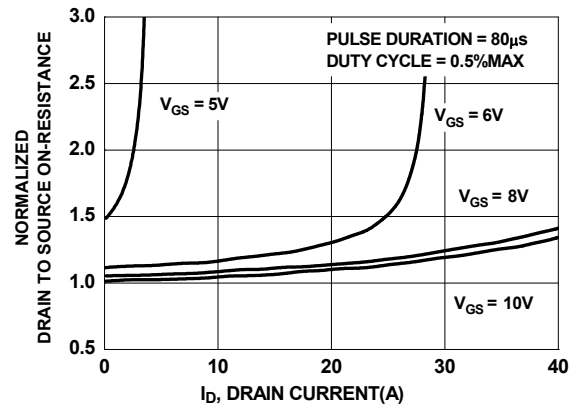


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

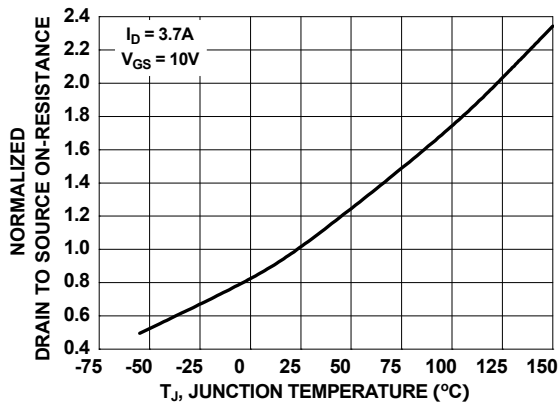


Figure 3. Normalized On Resistance vs Junction Temperature

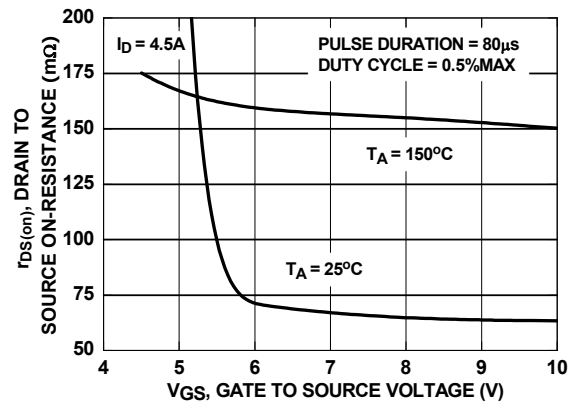


Figure 4. On-Resistance vs Gate to Source Voltage

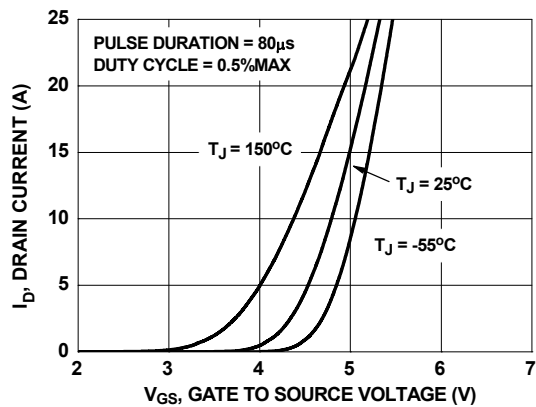


Figure 5. Transfer Characteristics

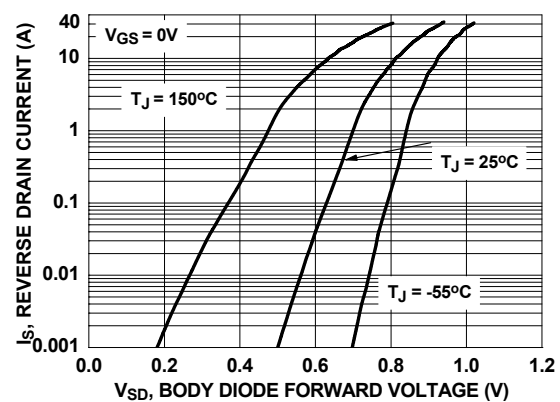


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

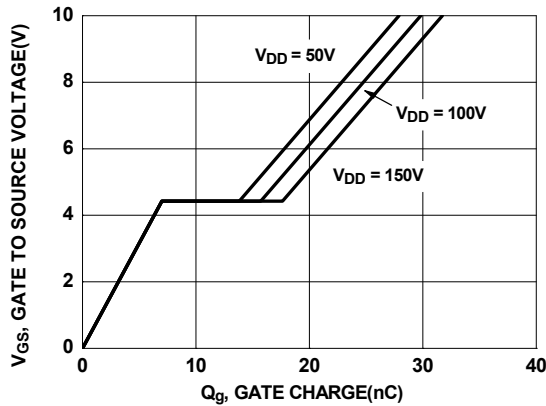


Figure 7. Gate Charge Characteristics

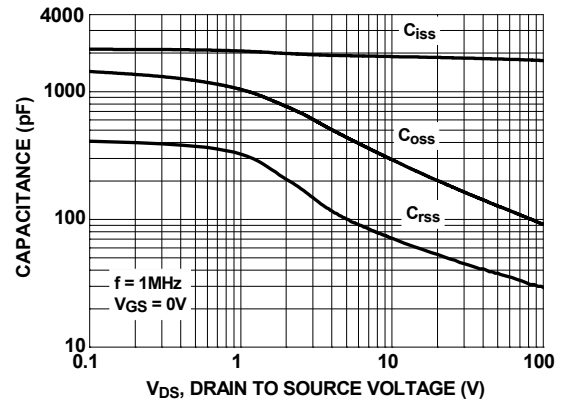


Figure 8. Capacitance vs Drain to Source Voltage

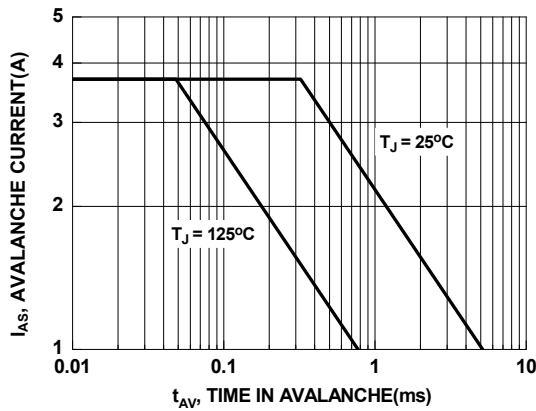


Figure 9. Unclamped Inductive Switching Capability

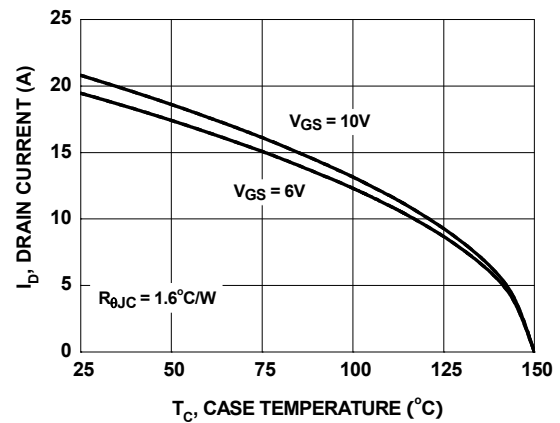


Figure 10. Maximum Continuous Drain Current vs Case Temperature

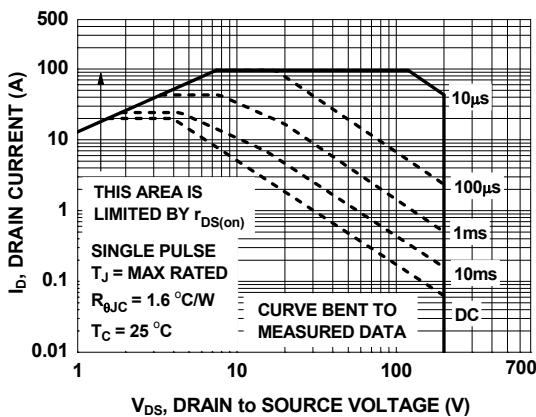


Figure 11. Forward Bias Safe Operating Area

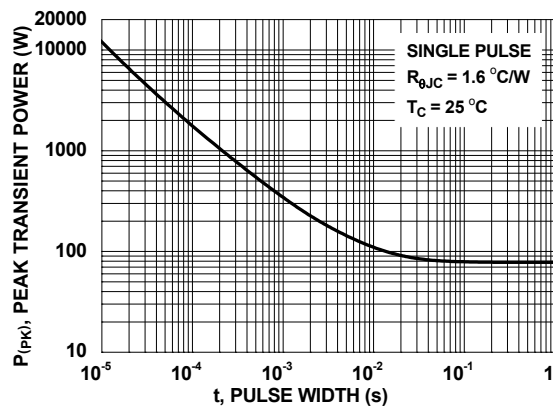


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

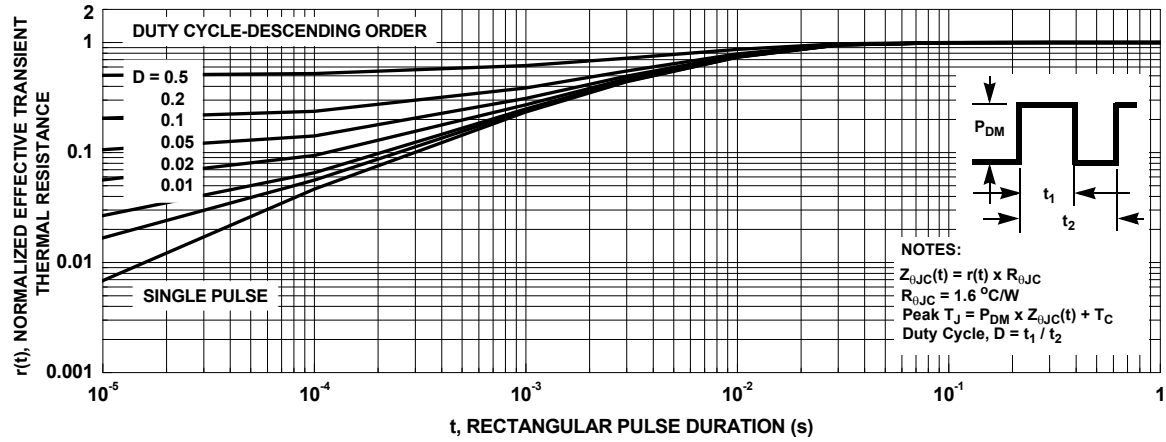
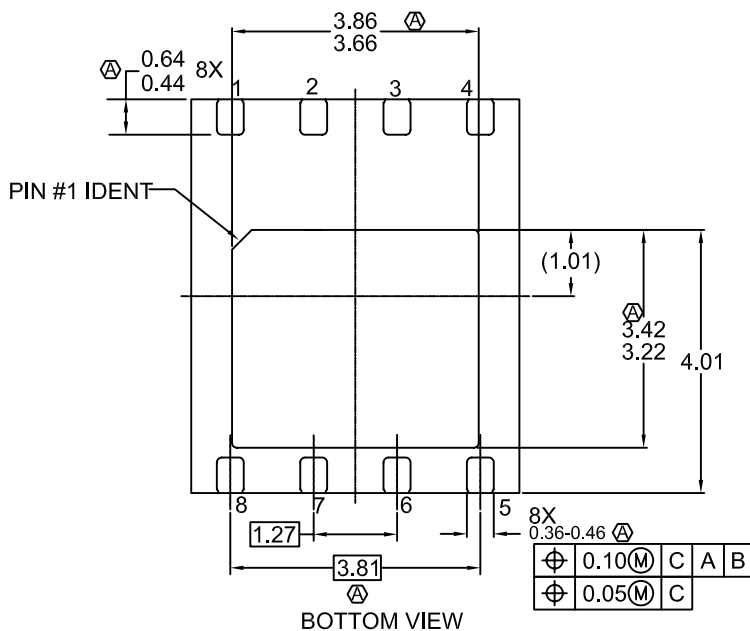
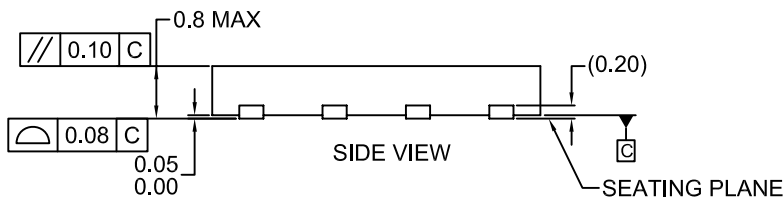
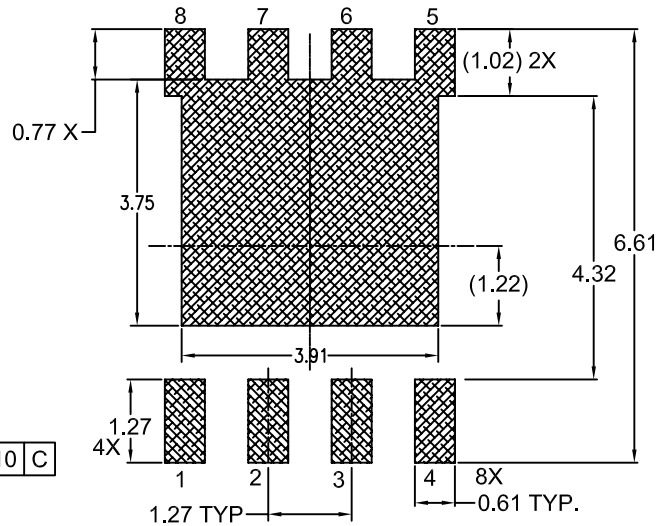
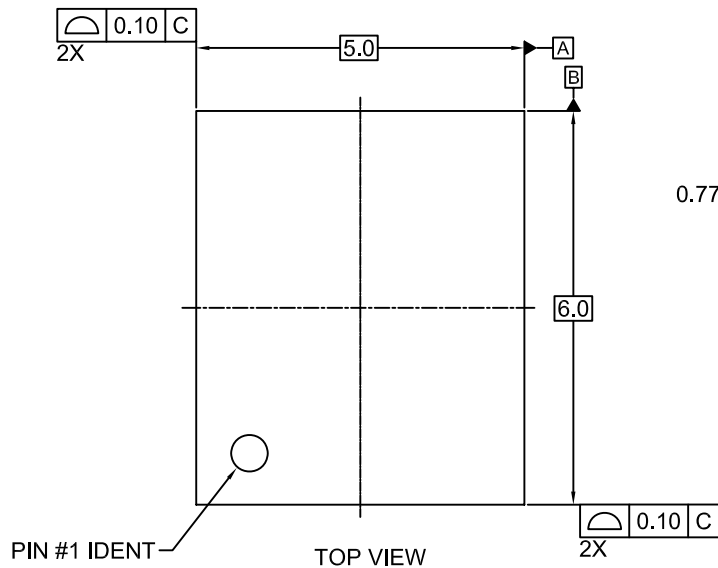


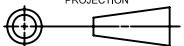
Figure 13. Junction-to-Case Transient Thermal Response Curve

REVISIONS			
NBR	DESCRIPTION	DATE	NAME/SITE
1	RELEASE TO DOCUMENT CONTROL	090305	David/FSPM
2	REVISE TO CORRECT DAP SIZE	080605	David/FSPM
3	I) REVISE TO CORRECT PKG THK II) REVISE THE PKG PROFILE TOLERANCE	210306	CK/FSPM
4	ADD IN LEAD LENGTH FOR LAND PATTERN	220908	LY/FSPM



NOTES:

- A DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
- D. TERMINALS 5,6,7 AND 8 ARE TIED TO THE EXPOSED PADDLE
- E. LANDPATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY
- F. DRAWING FILENAME: MKT-MLP08Grev4

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ENGR. CHK.	DAVID	01 Nov 08				
PROJECTION			SCALE	SIZE	DRAWING NUMBER	REV
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MM						
DO NOT SCALE DRAWING				SHEET 1 of 1		

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